## <u>SENSITRON</u> SEMICONDUCTOR

TECHNICAL DATA DATASHEET 1138, REV. D

# HV MOSFET Power Module Data Sheet

DESCRIPTION: 3000 VOLT, 1.0 AMP, INDUSTRIAL MOSFET POWER MODULE

#### **ELECTRICAL CHARACTERISTICS**

(AT Tj=25°C UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
POWER MOSFETS Q1,,6						
Drain-to-Source Breakdown Voltage for each one of Q1,2,,6	V <sub>(BR)DSS</sub>	$V_{GS}$ =0V,I <sub>D</sub> =0.5 mA, T <sub>i</sub> = 25 °C	1000	-	-	V
Drain-to-Source Leakage Current	I <sub>DSS</sub>	$ \begin{array}{l} V_{GS}{=}0V, \\ V_{DS}{=}1000V, \ \ T_{j} = 25\ ^{\circ}C \\ V_{DS}{=}1000V, \ \ T_{j} = 125\ ^{\circ}C \end{array} $	-	-	0.250 2	mA
Continuous Drain Current	I <sub>D</sub>	V <sub>GS</sub> =10V	-	-	1	А
Maximum Pulsed Drain Current <sup>(1)</sup>	I <sub>DM</sub>	T <sub>C</sub> = 25 °C	-	-	4	A
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ $I_D = 0.50 \text{mA}$	2.0	-	4.0	V
Static Drain-to-Source On Resistance	R <sub>DS</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 0.80 \text{ A}$	-		11.0	Ω
Input Capacitance Output Capacitance Reverse Transfer Cap.	C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	$V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1 MHz	-	500 52 17	-	pF
Total Gate Charge	Q <sub>G</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A},$ $V_{DD} = 400 \text{ V}$			38	nC
Turn-on Delay Rise Time Turn-off Delay Fall Time	$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	$V_{DD} = 500 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$ $I_D = 1.0 \text{ A}$	-	10 17 58 31	-	ns
Junction to Base Thermal Resistance	R <sub>thjc</sub>				3.7	°C/W
Nominal Gate-to-source Zener Breakdown Voltage, I <sub>Z</sub> = 1mA	Vz		±17.5	±18.0	±19.0	V
Operating and Storage Junction Temperature	T <sub>j</sub>		-40		100	°C
Operating Case Temperature	Ti		-40		100	°C
Pin-To-Base plate Voltage Isolation	V <sub>iso</sub>	1 minute, at sea level			10,000	V
DIODE CHARACTERISTICSD1,						
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 1A	-	-	1.1	V
Reverse Recovery Time	t <sub>rr</sub>	$T_j = 25 \text{ °C}, I_F = 1 \text{ A},$ di/dt = 50 A/ µs, V <sub>rr</sub> =400V	-	-	150	ns
GATE DRIVE MOSFETs Q7,,	18 <sup>(1)</sup> CHAF	RACTERISTICS	•	•	•	
Turn-On Time	t <sub>on</sub>		-	-	20	ns
Turn-Off Time	t <sub>off</sub>		-	-	20	ns

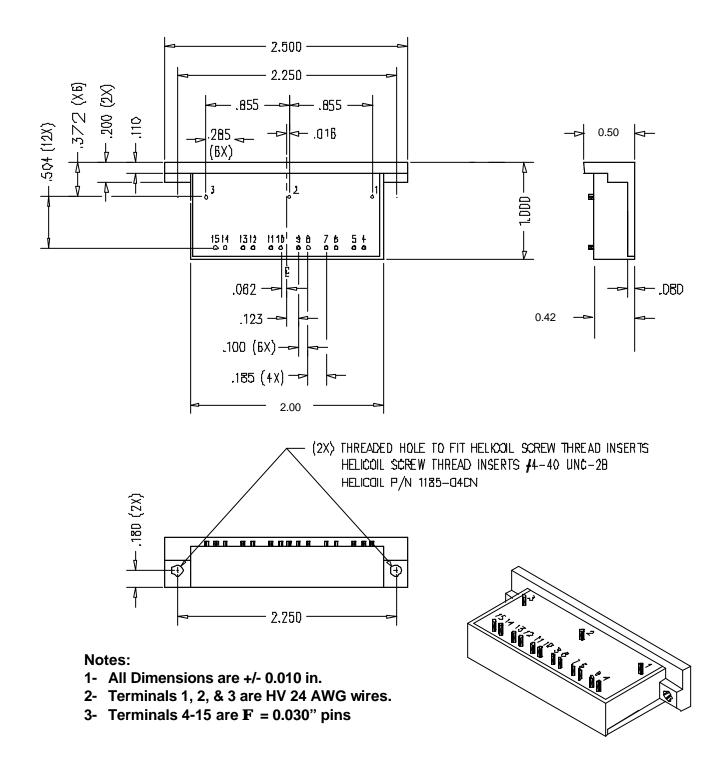
Notes,

1- Type 2N7002 or similar.

• 221 West Industry Court □ Deer Park, NY 11729-4681 □ Phone (631) 586 7600 Fax (631) 242 9798 •
• World Wide Web Site - www.sensitron.com • E-Mail Address - sales@sensitron.com •

#### SENSITRON TECHNICAL DATA DATASHEET 1138, REV. D

### **MECHANICAL DRAWING - In inches**





#### **TECHNICAL DATA**

#### DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.